

## ABSTRACT

The present invention provides a process control method in spin etching capable of realizing uniformity in etching amount in etching treatment for even wafers each having various conditions, and achieving  
5 uniformity of thickness values among etched wafers. In the present invention, weight of a wafer before etching is measured in units of 1/1000 g, followed by predetermined etching treatment in a spin etching section. Thereafter, weight of the wafer is again measured in units of 1/1000 g after  
10 rinsing and drying treatment of the wafer, and then an actual etching amount is calculated from a difference between weight before and after etching of the wafer, confirming an etching rate each time etching to thereby control an etching time.